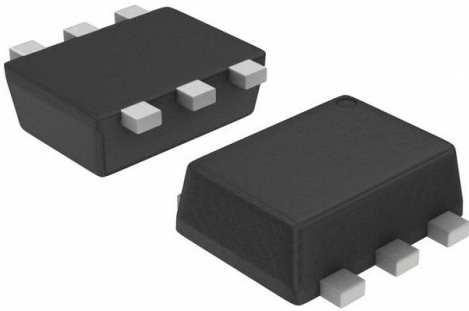


NSBC124XDXV6T1G Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	NSBC124XDXV6T1G-DG
Manufacturer	onsemi
Manufacturer Product Number	NSBC124XDXV6T1G
Description	TRANS PREBIAS 2NPN 50V SOT563
Detailed Description	Pre-Biased Bipolar Transistor (BJT) 2 NPN - Pre-Biased (Dual) 50V 100mA 500mW Surface Mount SOT-563



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

NSBC124XDXV6T1G

Series:

-

Transistor Type:

2 NPN - Pre-Biased (Dual)

Voltage - Collector Emitter Breakdown (Max):

50V

Resistor - Emitter Base (R2):

47kOhms

Vce Saturation (Max) @ Ib, Ic:

250mV @ 1mA, 10mA

Frequency - Transition:

-

Mounting Type:

Surface Mount

Supplier Device Package:

SOT-563

Manufacturer:

onsemi

Product Status:

Active

Current - Collector (Ic) (Max):

100mA

Resistor - Base (R1):

22kOhms

DC Current Gain (hFE) (Min) @ Ic, Vce:

80 @ 5mA, 10V

Current - Collector Cutoff (Max):

500nA

Power - Max:

500mW

Package / Case:

SOT-563, SOT-666

Base Product Number:

NSBC124

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

Dual NPN Bias Resistor Transistors

R1 = 22 k Ω , R2 = 47 k Ω

NPN Transistors with Monolithic Bias Resistor Network

MUN5234DW1, NSBC124XDXV6

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

(T_A = 25°C, common for Q₁ and Q₂, unless otherwise noted)

Symbol	Rating	Max	Unit
V _{CBO}	Collector-Base Voltage	50	Vdc
V _{CEO}	Collector-Emitter Voltage	50	Vdc
I _C	Collector Current – Continuous	100	mAdc
V _{IN(fwd)}	Input Forward Voltage	40	Vdc
V _{IN(rev)}	Input Reverse Voltage	7	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

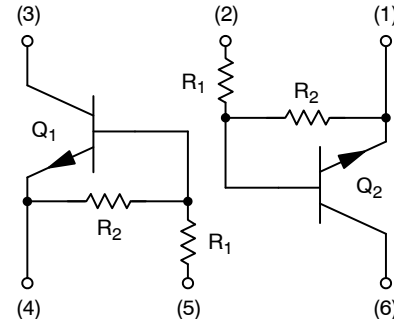


SOT-363
CASE 419B

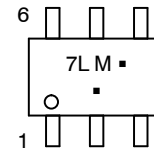


SOT-563
CASE 463A

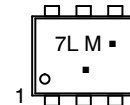
PIN CONNECTIONS



MARKING DIAGRAMS



SOT-363
CASE 419B



SOT-563
CASE 463A

7L = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MUN5234DW1T1G	SOT-363	3,000 / Tape & Reel
NSBC124XDXV6T1G	SOT-563	4,000 / Tape & Reel
NSVBC124XDXV6T1G	SOT-563	4,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MUN5234DW1, NSBC124XDXV6**THERMAL CHARACTERISTICS**

Symbol	Characteristic	Max	Unit
--------	----------------	-----	------

MUN5234DW1 (SOT-363) ONE JUNCTION HEATED

P _D	Total Device Dissipation T _A = 25°C (Note 1)	187	mW
	(Note 2) Derate above 25°C (Note 1)	256 1.5	mW/°C
R _{θJA}	Thermal Resistance, Junction to Ambient (Note 1)	670	°C/W
		490	

MUN5234DW1 (SOT-363) BOTH JUNCTION HEATED (Note 3)

P _D	Total Device Dissipation T _A = 25°C (Note 1)	250	mW
	(Note 2) Derate above 25°C (Note 1)	385 2.0	mW/°C
R _{θJA}	Thermal Resistance, Junction to Ambient (Note 1)	493	°C/W
		325	
R _{θJL}	Thermal Resistance, Junction to Lead (Note 1)	188	°C/W
	(Note 2)	208	
T _J , T _{stg}	Junction and Storage Temperature Range	-55 to +150	°C

NSBC124XDXV6 (SOT-563) ONE JUNCTION HEATED

P _D	Total Device Dissipation T _A = 25°C (Note 1)	357	mW
	Derate above 25°C (Note 1)	2.9	mW/°C
R _{θJA}	Thermal Resistance, Junction to Ambient (Note 1)	350	°C/W

NSBC124XDXV6 (SOT-563) BOTH JUNCTION HEATED (Note 3)

P _D	Total Device Dissipation T _A = 25°C (Note 1)	500	mW
	Derate above 25°C (Note 1)	4.0	mW/°C
R _{θJA}	Thermal Resistance, Junction to Ambient (Note 1)	250	°C/W
T _J , T _{stg}	Junction and Storage Temperature Range	-55 to +150	°C

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 × 1.0 Inch Pad.
- Both junction heated values assume total power is sum of two equally powered channels.

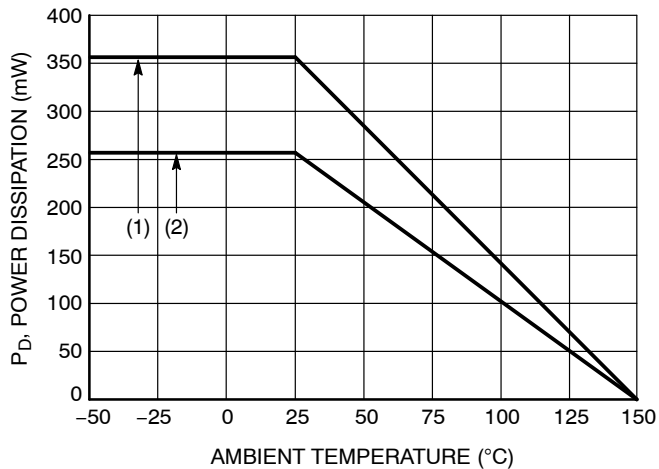
MUN5234DW1, NSBC124XDXV6**ELECTRICAL CHARACTERISTICS** ($T_A = 25^\circ\text{C}$, common for Q_1 and Q_2 , unless otherwise noted)

Symbol	Characteristic	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
I_{CBO}	Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}$, $I_E = 0$)	-	-	100	nAdc
I_{CEO}	Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}$, $I_B = 0$)	-	-	500	nAdc
I_{EBO}	Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}$, $I_C = 0$)	-	-	0.13	mAdc
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C = 10\ \mu\text{A}$, $I_E = 0$)	50	-	-	Vdc
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage (Note 4) ($I_C = 2.0\text{ mA}$, $I_B = 0$)	50	-	-	Vdc

ON CHARACTERISTICS

h_{FE}	DC Current Gain (Note 4) ($I_C = 5.0\text{ mA}$, $V_{CE} = 10\text{ V}$)	80	150	-	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage (Note 4) ($I_C = 10\text{ mA}$, $I_B = 1.0\text{ mA}$)	-	-	0.25	V
$V_{i(off)}$	Input Voltage (Off) ($V_{CE} = 5.0\text{ V}$, $I_C = 100\ \mu\text{A}$)	-	0.8	-	Vdc
$V_{i(on)}$	Input Voltage (On) ($V_{CE} = 0.2\text{ V}$, $I_C = 3.0\text{ mA}$)	-	1.3	-	Vdc
V_{OL}	Output Voltage (On) ($V_{CC} = 5.0\text{ V}$, $V_B = 2.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$)	-	-	0.2	Vdc
V_{OH}	Output Voltage (Off) ($V_{CC} = 5.0\text{ V}$, $V_B = 0.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$)	4.9	-	-	Vdc
R1	Input Resistor	15.4	22	28.6	$\text{k}\Omega$
R_1/R_2	Resistor Ratio	0.38	0.47	0.56	

4. Pulsed Condition: Pulse Width = 300 ms, Duty Cycle \leq 2%.



(1) SOT-363; 1.0 x 1.0 Inch Pad
(2) SOT-563; Minimum Pad

Figure 1. Derating Curve

MUN5234DW1, NSBC124XDXV6

TYPICAL CHARACTERISTICS MUN5234DW1, NSBC124XDXV6

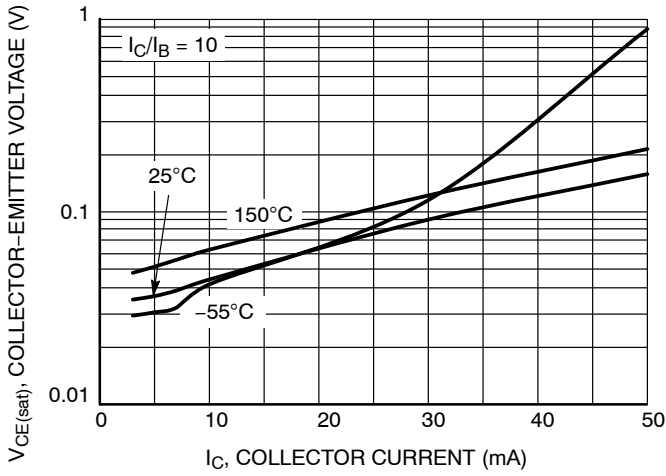


Figure 2. $V_{CE(sat)}$ vs. I_C

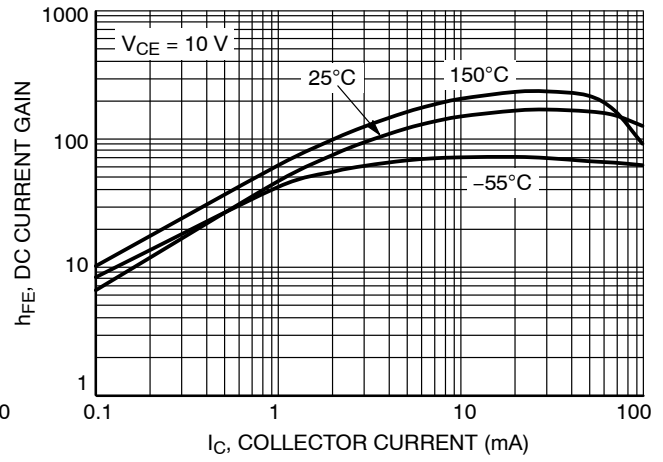


Figure 3. DC Current Gain

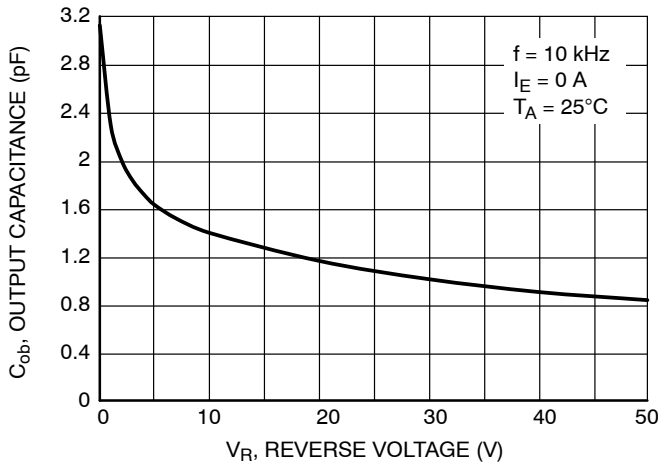


Figure 4. Output Capacitance

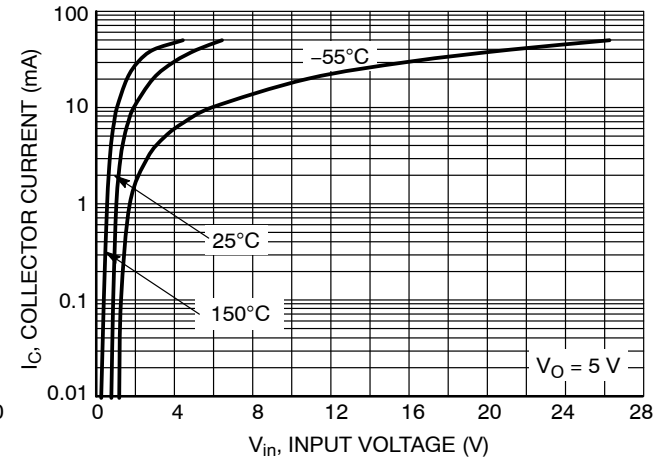


Figure 5. Output Current vs. Input Voltage

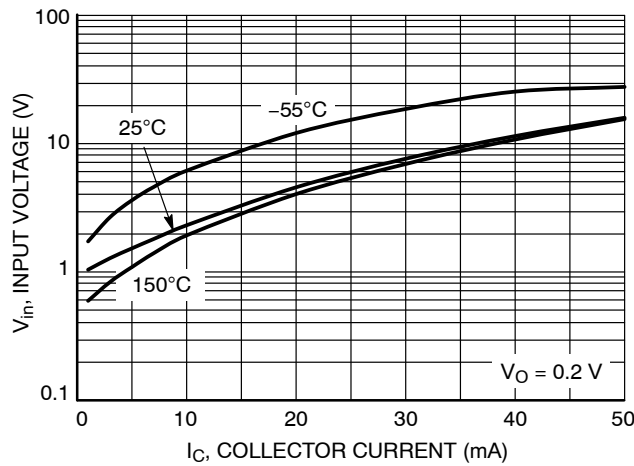


Figure 6. Input Voltage vs. Output Current



**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**

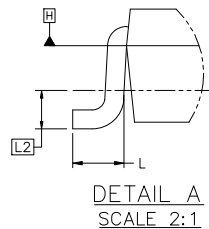
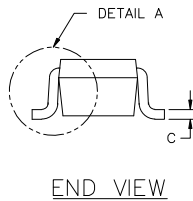
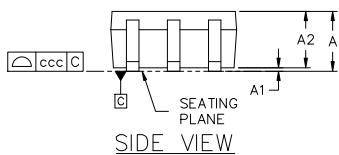
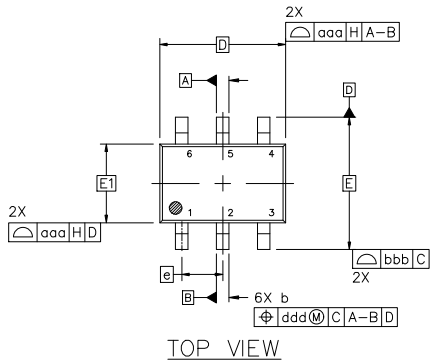


SC-88 2.00x1.25x0.90, 0.65P
CASE 419B-02
ISSUE Z

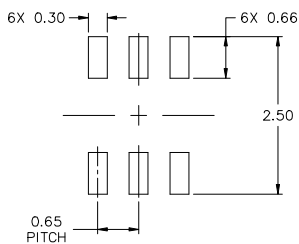
DATE 18 APR 2024

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

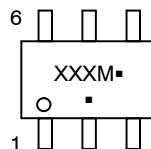


DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.00	---	0.10
A2	0.70	0.90	1.00
b	0.15	0.20	0.25
c	0.08	0.15	0.22
D	2.00 BSC		
E	2.10 BSC		
E1	1.25 BSC		
e	0.65 BSC		
L	0.26	0.36	0.46
L2	0.15 BSC		
aaa	0.15		
bbb	0.30		
ccc	0.10		
ddd	0.10		



* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SC-88 2.00x1.25x0.90, 0.65P
CASE 419B-02
ISSUE Z

DATE 18 APR 2024

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. IOUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**

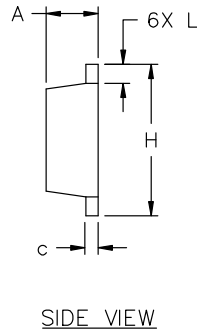
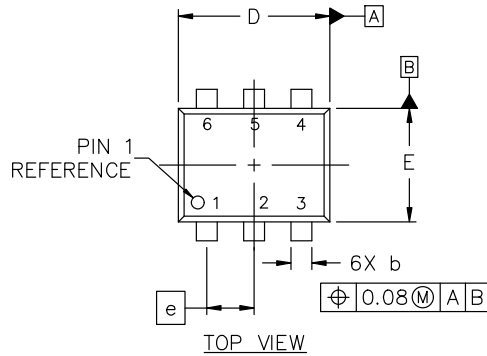


SOT-563-6 1.60x1.20x0.55, 0.50P
CASE 463A
ISSUE J

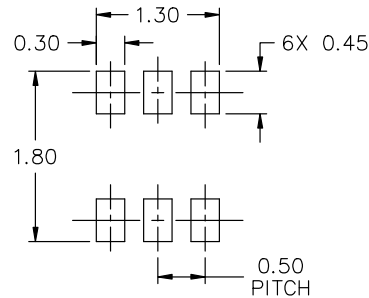
DATE 15 FEB 2024

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.50	1.60	1.70
E	1.10	1.20	1.30
e	0.50 BSC		
H	1.50	1.60	1.70
L	0.10	0.20	0.30



STYLE 1:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

STYLE 2:
PIN 1. EMITTER 1
2. EMITTER 2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1

STYLE 3:
PIN 1. CATHODE 1
2. CATHODE 1
3. ANODE/ANODE 2
4. CATHODE 2
5. CATHODE 2
6. ANODE/ANODE 1

STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE
4. ANODE
5. CATHODE
6. CATHODE

STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

STYLE 8:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 9:
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2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

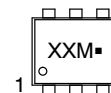
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2. N/C
3. CATHODE 2
4. ANODE 2
5. N/C
6. ANODE 1

STYLE 11:
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2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Month Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	SOT-563-6 1.60x1.20x0.55, 0.50P	PAGE 1 OF 1

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